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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Bohumil Lojek

PATENT APPLICATION

Serial No.: 10/773,059

Group Art Unit: 2818

Filed: February 4 , 2004

Examiner:

For: NON-VOLATILE MEMORY ARRAY WITH SIMULTANEOUS
WRITE AND ERASE FEATURE

Supplemental Information Disclosure Statement

Hon. Commissioner for Patents
Alexandria, VA 22313

Sir:

The following information is submitted in compliance with Applicant's duty of disclosure under 37 CFR § 1.56. A copy of the reference is enclosed.

Other Reference

B. Eitan et al. (School of Applied Science and Technology, The Hebrew University of Jerusalem, Jerusalem, Israel), *Impact Ionization at Very Low Voltages in Silicon*, J. Appl. Phys. 53(2), February 1982, pp. 1244-1247.

This statement is believed to be filed before the mailing date of a first Office action on the merits. Applicant respectfully requests consideration by the PTO of the submitted information.

CERTIFICATE OF MAILING

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

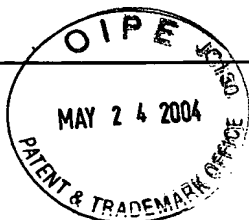
Signed: Sally Azevedo
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Date: May 20, 2004

Respectfully submitted,

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FORM PTO-1449	Atty. Docket No. ATM-275	Serial No. 10/773,059
LIST OF PRIOR ART CITED BY APPLICANT	Applicants: Bohumil Lojek	
	Filing Date: Feb. 4, 2004	Group: 2818



U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Name	Class	Sub Class	Filing Date
	AA					
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FOREIGN PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Country	Class	Sub Class	Translation Yes No
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	AL					
	AM					
	AN					

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AO	B. Eitan et al. (School of Applied Science and Technology, The Hebrew University of Jerusalem, Jerusalem, Israel), <i>Impact Ionization at Very Low Voltages in Silicon</i> , J. Appl. Phys. 53(2), February 1982, pp. 1244-1247.
	AP	

EXAMINER:

DATE CONSIDERED:

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.